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500.40010X00

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): K. OHNISHI et al  
Serial No.: 09/829,969  
Filed: April 11, 2001  
For: SEMICONDUCTOR DEVICE AND PROCESS FOR  
PRODUCING THE SAME  
Group: 2818  
Examiner: M. TRAN

**AMENDMENT**

**MS: AMENDMENTS (Fee)**  
Commissioner For Patents  
POB 1450  
Alexandria, VA 22313-1450

June 6, 2003

RECEIVED  
JUN 11 2003  
TECHNOLOGY CENTER 2800

Sir:

In response to the Office Action dated February 10, 2003, the period of response for which extension of time is requested in the attached Petition for Extension of Time, the following amendments and remarks are respectfully submitted in connection with the above-identified application.

**IN THE CLAIMS:**

Please **amend** claims 1, 4, 5, 8, 25, 28, 29, 31 and 33 to read as follows:

1. (Twice Amended) A semiconductor device with an MOS transistor, wherein a gate electrode of the MOS transistor is provided as a stacked structure comprising a silicon layer, a metal silicide layer, a metal nitride layer and a metallic layer, formed